



7/12/2007

**PRODUCT RELIABILITY REPORT
FOR**

DS2436, Rev C7 (8")

Dallas Semiconductor

**4401 South Beltwood Parkway
Dallas, TX 75244-3292**

Prepared by:

**Ken Wendel
Reliability Engineering Manager
Dallas Semiconductor
4401 South Beltwood Pkwy.
Dallas, TX 75244-3292
Email : ken.wendel@dalsemi.com
ph: 972-371-3726
fax: 972-371-6016
mbl: 214-435-6610**

Conclusion:

The following qualification successfully meets the quality and reliability standards required of all Dallas Semiconductor products:

DS2436, Rev C7 (8")

In addition, Dallas Semiconductor's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at <http://www.maxim-ic.com/TechSupport/dsreliability.html>.

Device Description:

A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l_datasheet3.cfm.

Reliability Derating:

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

$$AfT = \exp((Ea/k) * (1/Tu - 1/Ts)) = tu/ts$$

AfT = Acceleration factor due to Temperature
tu = Time at use temperature (e.g. 55°C)
ts = Time at stress temperature (e.g. 125°C)
k = Boltzmann's Constant (8.617 x 10⁻⁵ eV/°K)
Tu = Temperature at Use (°K)
Ts = Temperature at Stress (°K)
Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

$$AfV = \exp(B * (Vs - Vu))$$

AfV = Acceleration factor due to Voltage
Vs = Stress Voltage (e.g. 7.0 volts)
Vu = Maximum Operating Voltage (e.g. 5.5 volts)
B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

$$Fr = X / (ts * AfV * AfT * N * 2)$$

X = Chi-Sq statistical upper limit
N = Life test sample size

Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

$$MTTF = 1/Fr$$

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

FAILURE RATE:	MTTF (YRS):	17978	FITS:	6.3
	DEVICE HOURS:	153000	FAILS:	0

Only data from Operating Life or similar stresses are used for this calculation.

The parameters used to calculate this failure rate are as follows:

Cf: 60%	Ea: 0.7	B: 0	Tu: 25 °C	Vu: 5.25 Volts
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The reliability data follows. At the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available and may contain some generic data. "*" after DATE CODE denotes specific product data and SEQ No. to identify specific line items in the report for comments when required.

Device Information:

Process:	EC6W-2P2M,HPVt,E2,ALOCOS:GOI,5in Reticles,Legacy Flow
Passivation:	NRL Laser w/Nov TEOS Oxide-Nitride
Die Size:	90 x 70
Number of Transistors:	26403
Interconnect:	Aluminum / 0.5% Copper
Gate Oxide Thickness:	150 Å

OPERATING LIFE

DESCRIPTION	DATE CODE/SEQ	CONDITION	READPOINT	QTY	FAILS	FA#
HIGH VOLTAGE LIFE	0011	125C, 6.0V (PSA) & 12.0V (PSB)	1000 HRS	153	0	
HIGH TEMP OP LIFE	0647	125C, 5.25 VOLTS	1000 HRS	45	0	
HIGH TEMP OP LIFE	0648	125C, 5.25 VOLTS	1000 HRS	45	0	
HIGH TEMP OP LIFE	0649	125C, 5.25 VOLTS	1000 HRS	45	0	
HIGH TEMP OP LIFE	0651	125C, 5.25 VOLTS	1000 HRS	45	0	
HIGH TEMP OP LIFE	0652	125C, 5.25 VOLTS	1000 HRS	45	0	
HIGH TEMP OP LIFE	0701	125C, 5.25 VOLTS	1000 HRS	45	0	
HIGH TEMP OP LIFE	0706	125C, 6.0 VOLTS	1000 HRS	77	0	
HIGH TEMP OP LIFE	0706	125C, 6.0 VOLTS	1000 HRS	77	0	
HIGH TEMP OP LIFE	0706	125C, 6.0 VOLTS	1000 HRS	77	0	
Total:					0	

W/E ENDURANCE AND DATA RET'N

DESCRIPTION	DATE CODE/SEQ	CONDITION	READPOINT	QTY	FAILS	FA#
WRITE CYCLE STRESS (KCYS)	0011	85 C, 6.0 V (PSA): 12.0 V (PSB)	30 KCYS	77	0	
STORAGE LIFE		125C	168 HRS	77	0	

STORAGE LIFE	0706	150C	1000 HRS	229	0
STORAGE LIFE	0706	150C	1000 HRS	229	0
STORAGE LIFE	0706	150C	1000 HRS	229	0
STORAGE LIFE	0706	150C	1000 HRS	230	0
STORAGE LIFE	0706	150C	1000 HRS	230	0
STORAGE LIFE	0706	150C	1000 HRS	230	0
			Total:		0

FAILURE RATE: **MTTF (YRS):** **17978** **FITS:** **6.3**
 DEVICE HOURS: **153000** **FAILS:** **0**